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**INFORMATION DISCLOSED  
STATEMENT BY APPLICANT**

*(use as many sheets as necessary)*

Sheet

1 of

<i>Complete if Known</i>	
Application Number	10/594,152
Confirmation Number	Unassigned
Filing Date	September 25, 2006
First Named Inventor	Hideomi KOINUMA et al.
Art Unit	Unassigned
Examiner Name	Unassigned
Attorney Docket Number	063111

## U.S. PATENT DOCUMENTS

## FOREIGN PATENT DOCUMENTS

## NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation <sup>6</sup>
/A.H./	1	English Translation of the International Preliminary Report on Patentability (Form PCT/IPEA/409) mailed January 18, 2007, in corresponding International Application No. PCT/JP2005/006199 with Form PCT/IB/338	

1. *What is the name of the author of the book?*

/Anthony Ho/

### **Data Considered**

12/03/2007

**EXAMINER'S SIGNATURE:** /Anthony H. T. / **DATE CONSIDERED:** 10/10/2019

<sup>1</sup>Applicant's unique citation designation number (optional). <sup>2</sup>See Kind Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov), MPEP 901.04 or in the comment box of this document. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST. 3). <sup>4</sup>For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup>Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup> Applicant is to indicate here if English language Translation is attached.

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

*(use as many sheets as necessary)*

Sheet	1	of	1	Attorney Docket Number	063111
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*Complete if Known*

Application Number	New Application
Confirmation Number	
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First Named Inventor	Hideomi KOINUMA et al.
Art Unit	
Examiner Name	

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code <sup>2</sup> (if known)		
/A.H./	1	US 6,326,640	B1	12-04-2001	Son Q. SHI et al.
/A.H./	2	US 2003/0160235	A1	08-28-2003	Katsura HIRAI
		US			
		US			

**FOREIGN PATENT DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Translation <sup>6</sup>
		Country Code <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)			
/A.H./	3	JP	9-232589	A	09-05-1997	Motorola Inc.	Abstract, cited in ISR
/A.H./	4	JP	2003-324202	A	11-14-2003	Konica Minolta Holdings Inc.	Abstract, cited in ISR

**NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation <sup>6</sup>
/A.H./	5	K. UENO et al.; "Van der Walls epitaxy on hydrogen-terminated Si(111) surfaces and investigation of its growth mechanism by atomic force microscope", Journal of Crystal Growth, Vol. 150, 1995, pp.1180-1185. Cited in the specification.	
/A.H./	6	Y. Y. LIN et al.; "Stacked Pentacene Layer Organic Thin-Film Transistors with Improved Characteristics", IEEE Electron Device Letters, Vol. 18, No. 12, December 1997, pp.606-608. Cited in the specification.	
/A.H./	7	Vikram C. SUNDAR et al.; "Elastomeric Transistor Stamps: Reversible Probing of Charge Transport in Organic Crystal"; Science, Vol. 303, March 12, 2004, pp.1644-1646. Cited in the specification.	
/A.H./	8	R. W. J. de BOER et al.; "Organic single-crystal field-effect transistors", Phys. Stat. Sol. (a), Vol. 201, No. 6, 2004, pp.1302-1331. Cited in the specification.	
/A.H./	9	International Search Report of PCT/JP2005/006199, date of mailing July 5, 2005.	

Examiner Signature	/Anthony Ho/	Date Considered	12/03/2007
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